

FOR USE BY ELECTRICIANS OVERSEAS :

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (Ta=25°C)					電気的特性 (Ta=25°C)										外形	備考	
				V _{CB0} (V)	V _{CE0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CB0} 最大値 (μA) V _{CE} (V)		直流又はパルスh _{FE} V _{CE} (V) I _C (mA)		バイアス V _{CE} (V) I _B (mA)		h _{FE}	h _{ie} h _{ie} * (Ω)	h _{re} h _{re} * (×10 ⁻⁴)	h _{oe} h _{oe} * (μS)			f _{αb} f _{αb} * (Mc)
1	2	3	4	5					6		7		8				9	10		11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CB0} MAXIMUM VALUE AND V_{CE} VALUE (CRITERIA FOR MEASURING I_{CB0})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CE}, I_B (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9 f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T.
 - 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11 OUTLINE
 - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO

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型名	社名	用途	構造	最大定格 (T _a = 25°C)					電気的特性 (T _a = 25°C)													外形	備考	
				V _{CEO} (V)	V _{CEO} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CEO} 最大値 (μA)	V _{CE} (V)	直流又はパルス I _C (mA)	バイアス V _{CE} (V)	I _E (mA)	h _{FE} *	h _{FE} *	h _{FE} *	h _{FE} *	f _α *	C _{ob} (pF)	r _{ab} h _{FE} (resl)* (Ω)				
2SC1655A	E 電	RF. LN	Si. E	16	3	30	150	175	0.1	10	100	3	10	6	-20	NF < 3dB (8V, 5mA, 500MHz)	8000*	C _{ob} 0.5	40*	320				
" 1890A	日立	AF	"	120	5	50	300	125	0.5	100	250-1200	12	2	12	-2		200*	1.5		138				
" 1913A	松下	PA	"	180	5	1A	15W (T _c =25°C)	150	100	180	65-330	10	150	10	-50		120*	<10		268				
" 1965A	三菱	"	"	40	4	2A	15W (T _c =25°C)	175	500	25	50	10	100			P ₀ = 6.5W (f = 175MHz, V _{CE} = 13.5V, P ₀ = 0.6W)				97B	エミッタ ケース接続			
" 2127A	新電元	SW	Si. T	200	6	10A	100W (T _c =25°C)	150	250	200	32	3	10A			t _{on} < 1μS, t _{off} < 0.5μS				102				
" 2128A	"	"	"	200	6	30A	200W (T _c =25°C)	150	500	200	22	3	30A			t _{on} < 1μS, t _{off} < 0.5μS				266				
2SC631A	ソニー	RF. AF. LN	Si. E	25	6	200	250	120	0.2	25	400	3	1	6	-0.1		36k	2.4	3.3	140*	4.5	C _{rs} 350pS	38	2SA704 (とコンパ)
" 632A	"	RF. LN	"	50	6	200	250	120	0.2	25	400	3	1	6	-0.1		36k	2.4	3.3	140*	4.5	C _{rs} 350pS	38	2SA705 (とコンパ)
" 633A	"	RF. Conv. Mix Osc. SW	"	25	6	200	250	120	0.2	25	400	3	1	6	-2	t _{on} < 60nS, t _{off} < 150nS	140*	4.5	C _{rs} 350pS	38	2SA677 (とコンパ)			
" 634A	"	"	"	50	6	200	250	120	0.2	25	400	3	1	6	-2	t _{on} < 60nS, t _{off} < 150nS	140*	4.5	C _{rs} 350pS	38	2SA678 (とコンパ)			
" 756A	"	RF. PA	Si. EMe	130	6	4A	10W (T _c =25°C)	175	1	50	100	2	100	10	-100					100*	45	C _{rs} 35pS	181	
" 806A	"	PA	Si. TMe	700	10.5	10A	125W (T _c =25°C)	150	5mA	500	40	3	2A	10	-500					5.5*	285	5	102	
" 867A	"	RF. PA	"	520	10	3A	48W (T _c =25°C)	150	50	50	80	3	100	10	-200					8.5*	90	12	100	
" 1664A	サンケン	PA	"	100	6	6A	40W (T _c =25°C)	150	10	100	1000	4	1A	10	-500					20*	75	12	99	
" 1741A	東洋電機	AF	Si. EP	50	5	500	400	125	0.5	30	82-390	3	100	5	-20					250*	5		138	
" 1871A	日 電	SW	Si. TMe	500	7	10A	100W (T _c =25°C)	150	100	400	>15	5	5A			t _{on} < 1μS, t _{off} < 1μS							102	
" 2337A	"	PA. SW	Si. E	150	4.5	10A	100W (T _c =25°C)	150	50	150	150	5	1A	5	-200	t _{on} = 0.2μS, t _{off} = 1.8μS	70*	150					102	2SA1007A (とコンパ)
" 2516A	"	SW	"	150	12	5A	30W (T _c =25°C)	150	10	80	40-200	5	3A			t _{on} < 0.5μS, t _{off} < 0.5μS							268	2SA1069A (とコンパ)
" 1627A	東 芝	AF. PA	"	80	5	400	800	150	0.1	50	70-240	2	50	10	-10					100*	10		241	2SA817A (とコンパ)
" 1708A	三 菱	AF. I.N. RF	Si. EP	120	5	50	200	125	0.1	70	250-1200	6	1	6	-1	V _{NO} < 170mV (10V, 1mA, I ₀ = 100kΩ, A _v = 80dB)	150*	1.8					138B	2SA847A (とコンパ)
" 1914A	"	AF. RF	"	120	5	50	200	125	0.1	70	250-1200	6	1	6	-1					150*	1.8		138B	
" 2126A	新電元	SW	Si. T	200	6	3A	30W (T _c =25°C)	150	250	200	42	3	3A			t _{on} < 1μS, t _{off} < 1μS							204	
" 2139A	東 芝	"	"	500	6	10A	100W (T _c =25°C)	150	100	400	>20	5	5A			t _{on} < 1μS, t _{off} < 1μS							102	
" 2230A	"	PA	"	200	5	100	800	150	0.1	200	120-400	10	10	10	-10					>50*	<7		241	
" 2231A	"	"	"	200	5	200	12W (T _c =25°C)	150	0.1	200	100-320	10	50	10	-50					>50*	<10		178	
" 2238A	"	"	Si. E	180	5	1.5A	25W (T _c =25°C)	150	1	160	70-240	5	100	10	-100					100*	25		268	2SA968A (とコンパ)
" 2238B	"	"	"	200	5	1.5A	25W (T _c =25°C)	150	1	160	70-240	5	100	10	-100					100*	25		268	2SA968B (とコンパ)